



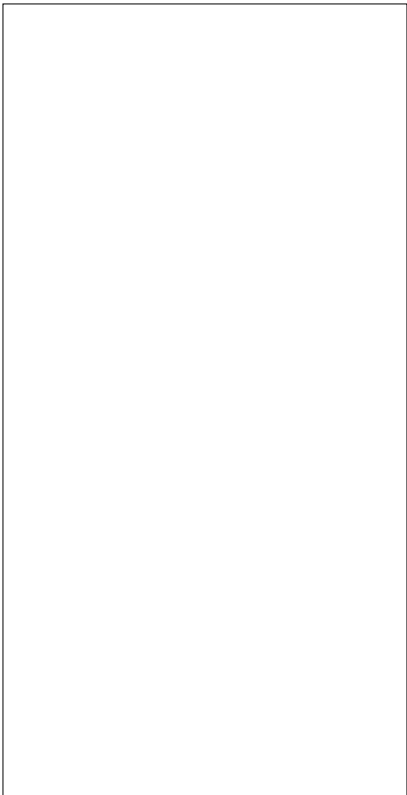
JCT151A-650RH 12A SCR

Rev.A.1.1

**DESCRIPTION:**

With high ability to withstand the shock loading of large current, JCT151A-650RH of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT151A-650RH provides a rated insulation voltage of 2500 V<sub>RMS</sub>, complying with UL standards (File ref: E252906).

Package TO-220A is RoHS compliant.



**MAIN FEATURES**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	12	A
V <sub>DRM</sub> /V <sub>R<sub>RRM</sub></sub>	650	V
I <sub>GT</sub>	"15	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	T <sub>stg</sub>	-40-150	
Operating junction temperature range	T <sub>j</sub>	-40-150	
Repetitive peak off-state voltage (T <sub>j</sub> =25 )	V <sub>DRM</sub>	650	V
Repetitive peak reverse voltage (T <sub>j</sub> =25 )	V <sub>R<sub>RRM</sub></sub>	650	V

Average on-state current (T<sub>c</sub> 0 R<sub>RRM</sub>

Peak gate current ( $t_p=20 \text{ s}$ , $T_j=150$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=150$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W



FIG.1: Maximum power dissipation versus RMS on-state current

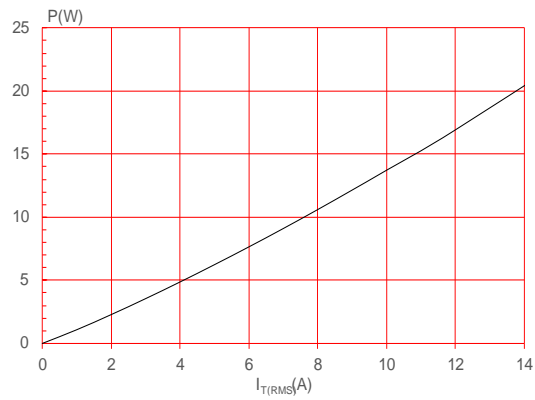


FIG.3: Surge peak on-state current versus number of cycles

FIG.2: RMS on-state current versus case temperature

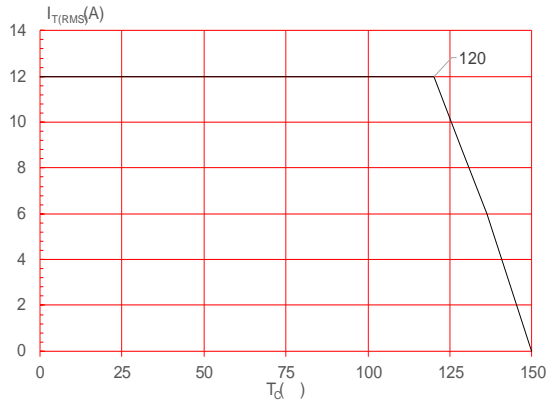
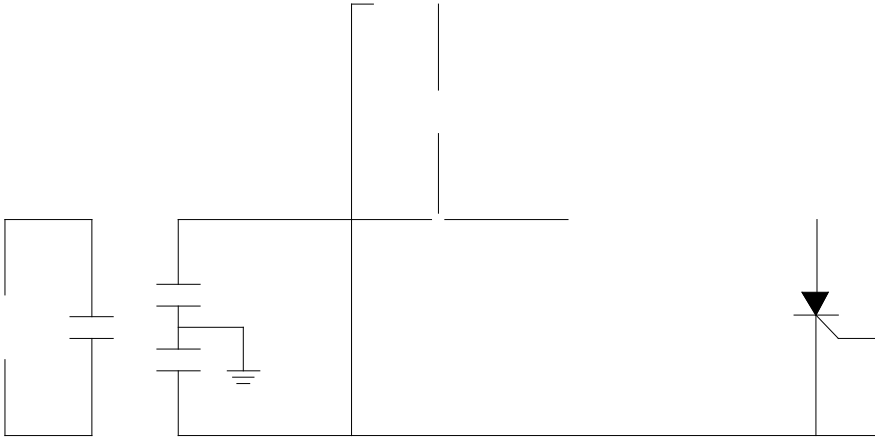


FIG.4: On-state characteristics

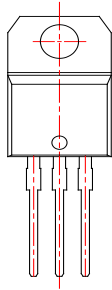
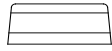
FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.




ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	
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PACKAGE MECHANICAL DATA



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